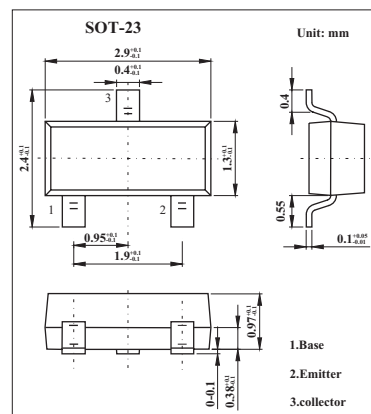


Silicon PNP Epitaxial Planar Type

2SC2404



■ Features

- Optimum for RF amplification of FM/AM radios
- High transition frequency f_T
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	30	V
Collector-emitter voltage	V_{CE0}	20	V
Emitter-base voltage	V_{EB0}	3	V
Collector current	I_C	15	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V_{CB0}	$I_C = 10 \mu\text{A}, I_E = 0$	30			V
Emitter-base voltage	V_{EB0}	$I_E = 10 \mu\text{A}, I_C = 0$	3			V
Base-emitter voltage	V_{BE}	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}$		0.72		V
Forward current transfer ratio	h_{FE}	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}$	65		260	
Transition frequency	f_T	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$	450	650		MHz
Reverse transfer capacitance	C_{re}	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$		0.8	1.0	pF
Power gain	G_P	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$		24		dB
Noise figure	NF	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$		3.3		dB

■ h_{FE} Classification

Marking	U	
Rank	C	D
h_{FE}	65~160	100~260